

新势力光电供应光电二极管(PIN), 用于将光信号转换为电信号, 形成光电效应/光电池。

技术特点:

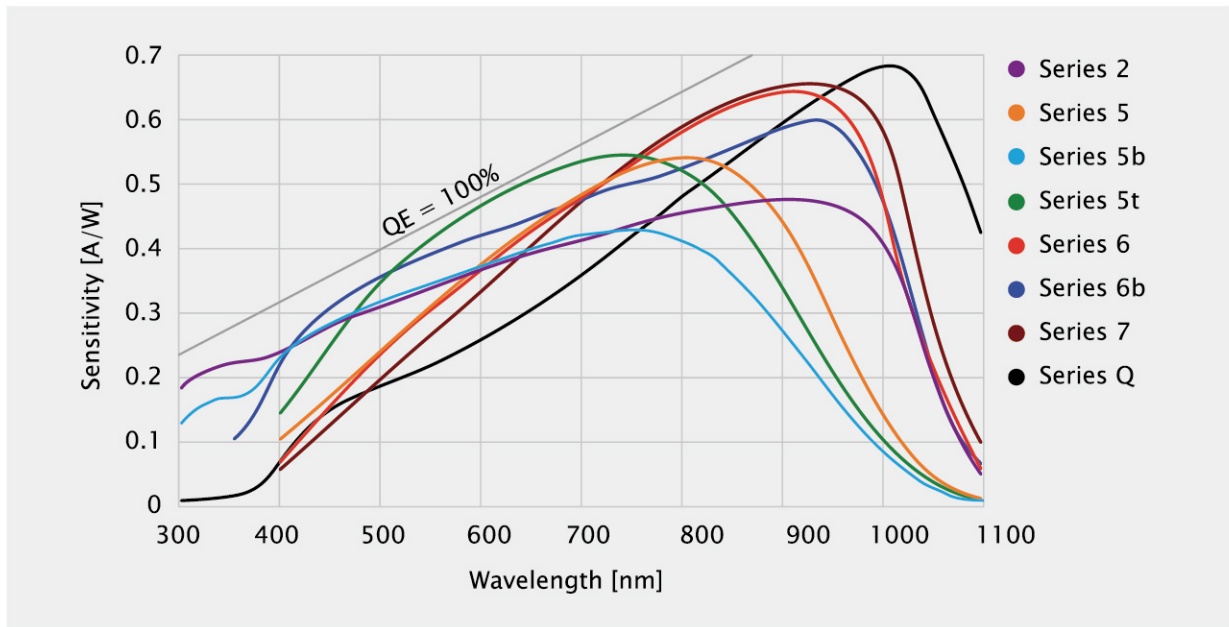
响应速度快、暗电流低、串扰低、反射低、寿命长、紫外增强、蓝光增强、红外增强。

产品应用:

安检设备、激光测距、工业控制、分析仪器、生物医疗、光通信、军事设备、航空航天。



PIN Series	Special features for Applications
Series-2 Optimized for 200-500nm	UV/Blue enhanced for analytical instruments, readout for scintillators.
Series-6b Optimized for 400-650nm	Blue/Green enhanced for photometric illuminometer.
Series-5b Optimized for 350-650nm	High-speed blue enhanced for high speed photometry.
Series-5t Optimized for 400-900nm	High-speed red-enhanced for high speed photometry.
Series-5 Optimized for 400-950nm	High-speed NIR-enhanced for high speed photometry.
Series-6 Optimized for 700-950nm	Low dark current, fast response for precision photometry.
Series-7 Optimized for 700-1100nm	Low capacity, full depletable for high energy physics.
Series-Q Optimized for 900-1100nm	Enhanced NIR sensitivity for YAG laser detection.



PIN光电二极管响应曲线图

激光器

光学测量

光学元件

太赫兹系统

▶ 光电探测器

单光子计数器

光学滤光片

可饱和吸收镜

光源

光纤

- 激光器
- 光学测量
- 光学元件
- 太赫兹系统

光电探测器 ◀

- 单光子计数器
- 光学滤光片
- 可饱和吸收镜
- 光源
- 光纤

Series 2: UV/Blue sensitive photodiodes					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	5V	410nm 5V 50Ω
		mm	mm ²	nA	ns
PS1-2	TO52	1.0×1.0	1	0.01	50
PS1-2	LCC6.1	1.0×1.0	1	0.01	50
PC5-2	TO5	∅2.52	5	0.3	150
PS7-2	TO5	2.66×2.66	7	0.4	200
PC10-2	TO5	∅3.57	10	1	300
PS13-2	TO5	3.5×3.5	13	1	300
PS33-2	TO8	5.7×5.7	33	2	600
PC50-2	BNC	∅7.98	50	5	1000
PS100-2	BNC	10×10	100	10	2000
PS100-2	CERpin	10×10	100	10	2000
Band pass filter modules: PC10-2 TO5i with center wavelength 254nm, 300nm, 350nm					
Series 6b: Blue/Green sensitive photodiodes					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	5V	410nm 5V 50Ω
		mm	mm ²	nA	ns
PS1-6b	TO52S1	1×1	1	0.05	10
PS1-6b	LCC6.1	1×1	1	0.05	10
PC5-6b	TO5	∅2.52	5	0.1	20
PS7-6b	TO5	2.7×2.7	7	0.15	25
PC10-6b	TO5	∅3.57	10	0.2	45
PS13-6b	TO5	3.5×3.5	13	0.25	50
PS33-6b	TO8	5.7×5.7	33	0.6	140
PS100-6b	LCC10S	10×10	100	1	200
PS100-6b	CERpinE	10×10	100	1	200
PS100-6b	CERpinG	10×10	100	1	200
Band pass filter modules: PR20-6b TO5i with center wavelength 488nm, 550nm, 633nm, 680nm					
Series 5b: High speed photodiodes (for blue-sensitive photodiodes)					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	3.5V	405nm 3.5V 50Ω
		mm	mm ²	nA	ns
PS1.0-5b	TO52S1	1.0×1.0	1	0.01	1.3
PS1.0-5b	LCC6.1	1.0×1.0	1	0.01	1.3
PS7-5b	TO5	2.7×2.7	7	0.5	5
PC10-5b	TO5	∅3.57	10	0.5	6
PS13-5b	TO5	3.5×3.5	13	1	6

Series 5t: High speed photodiodes for low voltages (for low operating voltages between 3 and 5 V, making them ideal for VIS and NIR applications in conjunction with CMOS components)					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	3.5V	850nm 3.5V 50Ω
		mm	mm ²	nA	ns
PS0.25-5t	LCC6.1	0.5×0.5	0.25	0.01	0.4
PS0.25-5t	SMD1206	0.5×0.5	0.25	0.01	0.4
PC0.55-5t	LCC6.1	∅0.84	0.55	0.01	1
PC0.55-5t	T1 3/4	∅0.84	0.55	0.01	1
PC0.55-5t	T1 3/4 black	∅0.84	0.55	0.01	1
PS1-5t	LCC6.1	1.0×1.0	1	0.01	1
PS7-5t	TO5	2.7×2.7	7	0.5	1
Series 5: High speed photodiodes (for fast rise times at low reverse voltages)					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	20V	850nm 20V 50Ω
		mm	mm ²	nA	ns
PS0.25-5	TO52S1	0.5×0.5	0.25	0.1	0.4
PS0.25-5	TO52S3	0.5×0.5	0.25	0.1	0.4
PS0.25-5	LCC6.1	0.5×0.5	0.25	0.1	0.4
PS0.25-5	SMD1206	0.5×0.5	0.25	0.1	0.4
PC0.55-5	TO52S1	∅0.84	0.55	0.2	1
PC0.55-5	LCC6.1	∅0.84	0.55	0.2	1
PS1.0-5	TO52S1	1.0×1.0	1	0.2	1.5
PS1.0-5	TO52S3	1.0×1.0	1	0.2	1.5
PS1.0-5	LCC6.1	1.0×1.0	1	0.2	1.5
PS7-5	TO5	2.7×2.7	7	0.5	2
PS11.9-5	TO5	3.45×3.45	11.9	1	3
PC20-5	TO8	∅5.05	20	2	3.5
PS33-5	TO8	5.7×5.7	33	2	3.5
PS100-5	LCC10S	10×10	100	2	5
PS100-5	CERpinG	10×10	100	2	5

激光器

光学测量

光学元件

太赫兹系统

▶ 光电探测器

单光子
计数器

光学滤光片

可饱和
吸收镜

光源

光纤

- 激光器
- 光学测量
- 光学元件**
- 太赫兹系统

- 光电探测器 ◀
- 单光子计数器
- 光学滤光片
- 可饱和吸收镜
- 光源
- 光纤

Series 6: IR photodiodes with min. dark current (for low-capacitance light detection as well as for α , β , γ and X-radiation detection)					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	10V	850nm 10V 50 Ω
		mm	mm ²	nA	ns
PC1-6	TO52S1	Ø1.13	1	0.05	10
PC1-6	TO52S3	Ø1.13	1	0.05	10
PC5-6	TO5	Ø2.52	5	0.1	13
PS7-6	TO5	2.66×2.66	7	0.1	15
PC10-6	TO5	Ø3.57	10	0.2	20
PS13-6	TO5	3.5×3.5	13	0.2	20
PC20-6	TO8	Ø5.05	20	0.3	25
PS33-6	TO8	5.7×5.7	33	0.4	25
PC50-6	TO8S	Ø7.98	50	0.5	30
PC100-6	BNC	Ø11.28	100	1	40
PS100-6	BNC	10×10	100	1	40
PS100-6	LCC10S	10×10	100	1	40
PS100-6	CERpinG	10×10	100	1	40
Series 7: IR photodiodes with fully depletable (very low capacitance levels)					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	10V	905nm 10V 50 Ω
		mm	mm ²	nA	ns
PC5-7	TO8i	Ø2.52	5	0.05	45
PC10-7	TO8i	Ø3.57	10	0.1	50
PC20-7	TO8Si	Ø5.05	20	0.2	50
PS100-7	LCC10G	10×10	100	1.5	50
Series Q: Photodiodes for 1064nm (specifically for laser rangefinders, laser-based targeting systems or any applications using YAG lasers or similar NIR radiation sources)					
Type No.		Active area		Dark current	Rise time
Chip	Package	Size	Area	150V	1064nm 150V 50 Ω
		mm	mm ²	nA	ns
PC10-Q	TO8i	Ø3.57	10	0.5	14
PC20-Q	TO8Si	Ø5.05	20	1	14
PS100-Q	LCC10G	10×10	100	80	14
PC50-Q	TO8Si	Ø8	50	2.5	14